

**FAIRCHILD**  
SEMICONDUCTOR®

**QFET™**

## FQP3N80C/FQPF3N80C

### 800V N-Channel MOSFET

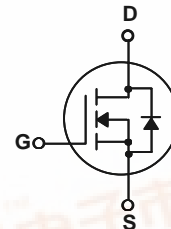
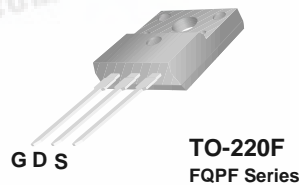
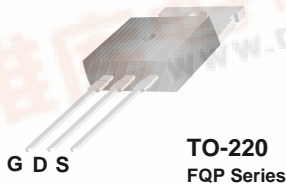
#### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supplies.

#### Features

- 3.0A, 800V,  $R_{DS(on)} = 4.8\Omega$  @  $V_{GS} = 10V$
- Low gate charge ( typical 13 nC)
- Low  $C_{rss}$  ( typical 5.5 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



#### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	FQP3N80C	FQPF3N80C	Units
$V_{DSS}$	Drain-Source Voltage	800		V
$I_D$	Drain Current - Continuous ( $T_C = 25^\circ\text{C}$ ) - Continuous ( $T_C = 100^\circ\text{C}$ )	3	3 *	A
		1.9	1.9 *	A
$I_{DM}$	Drain Current - Pulsed (Note 1)	12	12 *	A
$V_{GSS}$	Gate-Source Voltage	$\pm 30$		V
$E_{AS}$	Single Pulsed Avalanche Energy (Note 2)	320		mJ
$I_{AR}$	Avalanche Current (Note 1)	3		A
$E_{AR}$	Repetitive Avalanche Energy (Note 1)	10.7		mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5		V/ns
$P_D$	Power Dissipation ( $T_C = 25^\circ\text{C}$ ) - Derate above $25^\circ\text{C}$	107	39	W
		0.85	0.31	W/ $^\circ\text{C}$
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150		$^\circ\text{C}$
$T_L$	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300		$^\circ\text{C}$

\* Drain current limited by maximum junction temperature.

#### Thermal Characteristics

Symbol	Parameter	FQP3N80C	FQPF3N80C	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	1.17	3.2	$^\circ\text{C}/\text{W}$
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink Typ.	0.5	--	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	62.5	62.5	$^\circ\text{C}/\text{W}$



## Electrical Characteristics

$T_C = 25^\circ\text{C}$  unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\ \mu\text{A}$	800	--	--	V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$	--	1	--	$\text{V}/^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 800\text{ V}, V_{GS} = 0\text{ V}$	--	--	10	$\mu\text{A}$
		$V_{DS} = 640\text{ V}, T_C = 125^\circ\text{C}$	--	--	100	$\mu\text{A}$
$I_{GSSF}$	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
$I_{GSSR}$	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\ \mu\text{A}$	3.0	--	5.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 1.5\text{ A}$	--	4.0	4.8	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 50\text{ V}, I_D = 1.5\text{ A}$ (Note 4)	--	3	--	S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	543	705	pF
$C_{oss}$	Output Capacitance		--	54	70	pF
$C_{rss}$	Reverse Transfer Capacitance		--	5.5	7.5	pF
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 400\text{ V}, I_D = 3\text{ A},$ $R_G = 25\ \Omega$	--	15	40	ns
$t_r$	Turn-On Rise Time		--	43.5	95	ns
$t_{d(off)}$	Turn-Off Delay Time		--	22.5	55	ns
$t_f$	Turn-Off Fall Time		(Note 4, 5)	--	32	75
$Q_g$	Total Gate Charge	$V_{DS} = 640\text{ V}, I_D = 3\text{ A},$ $V_{GS} = 10\text{ V}$	--	13	16.5	nC
$Q_{gs}$	Gate-Source Charge		--	3.4	--	nC
$Q_{gd}$	Gate-Drain Charge		(Note 4, 5)	--	5.8	--
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain-Source Diode Forward Current		--	--	3.0	A
$I_{SM}$	Maximum Pulsed Drain-Source Diode Forward Current		--	--	12	A
$V_{SD}$	Drain-Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = 3.0\text{ A}$	--	--	1.4	V
$t_{rr}$	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_S = 3.0\text{ A},$	--	642	--	ns
$Q_{rr}$	Reverse Recovery Charge	$dI_F / dt = 100\text{ A}/\mu\text{s}$ (Note 4)	--	4.0	--	$\mu\text{C}$

**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2.  $L = 67\text{mH}, I_{AS} = 3.0\text{A}, V_{DD} = 50\text{V}, R_G = 25\ \Omega$ , Starting  $T_J = 25^\circ\text{C}$
3.  $I_{SD} \leq 3\text{A}, di/dt \leq 200\text{A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , Starting  $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse width  $\leq 300\ \mu\text{s}$ , Duty cycle  $\leq 2\%$
5. Essentially independent of operating temperature

## Typical Characteristics

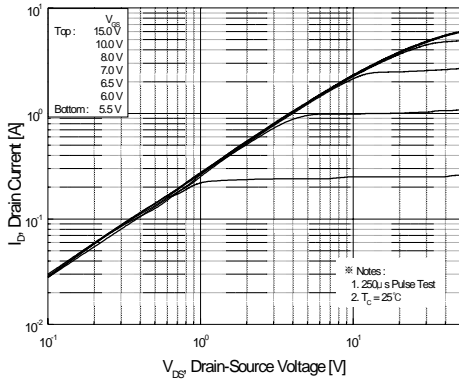


Figure 1. On-Region Characteristics

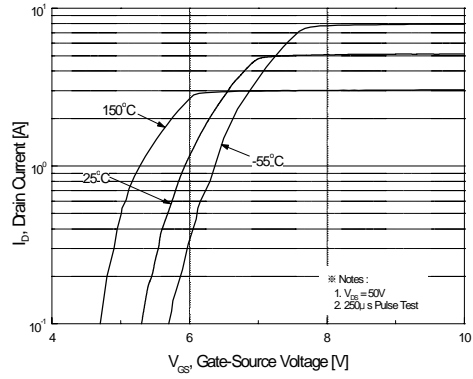


Figure 2. Transfer Characteristics

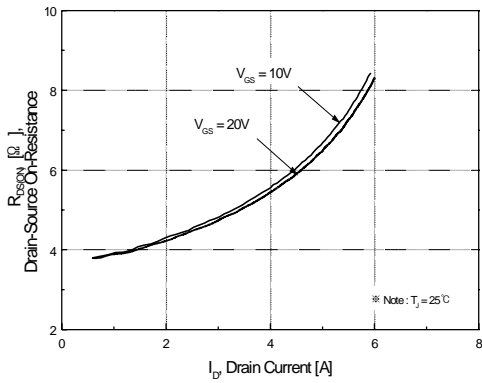


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

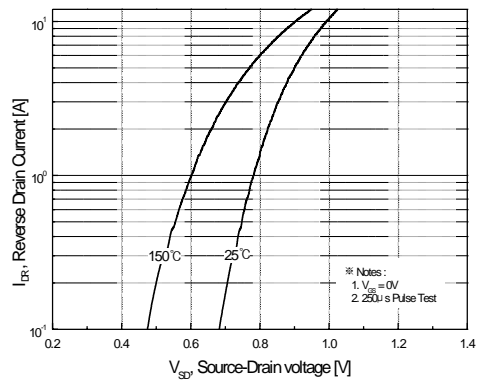


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

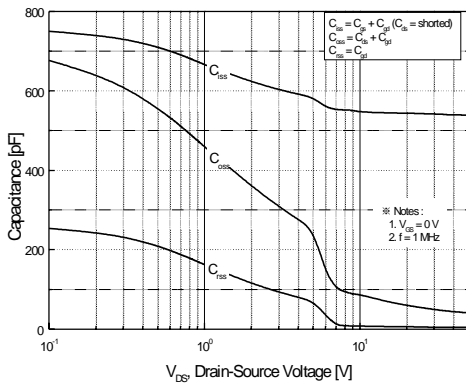


Figure 5. Capacitance Characteristics

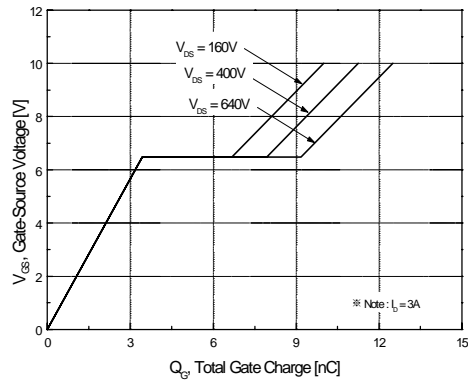
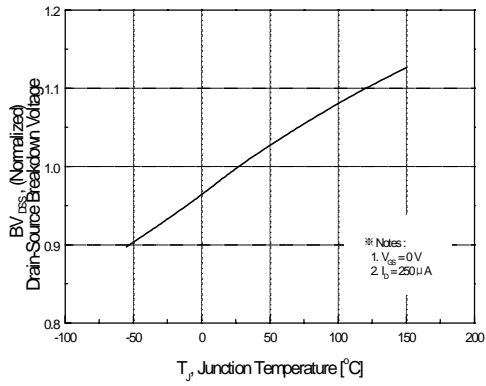
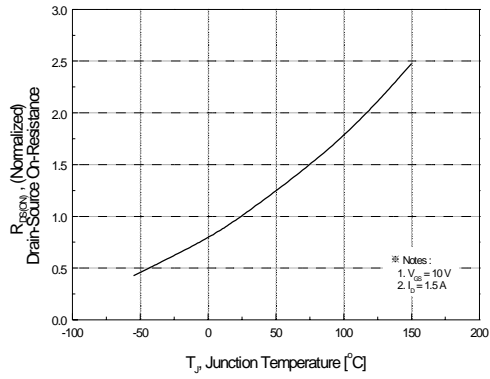


Figure 6. Gate Charge Characteristics

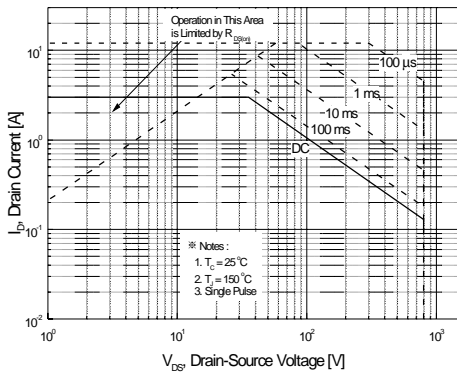
**Typical Characteristics** (Continued)



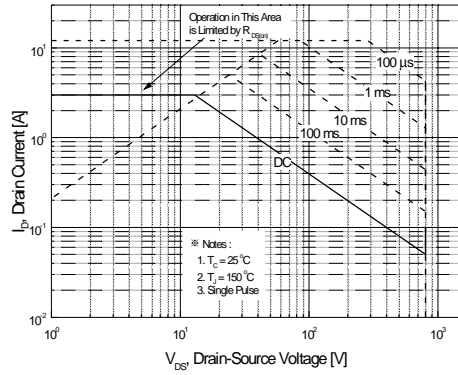
**Figure 7. Breakdown Voltage Variation vs Temperature**



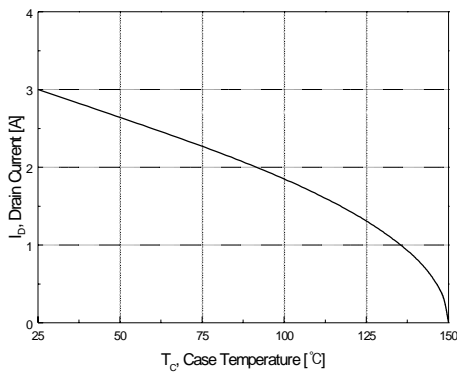
**Figure 8. On-Resistance Variation vs Temperature**



**Figure 9-1. Maximum Safe Operating Area for FQP3N80C**

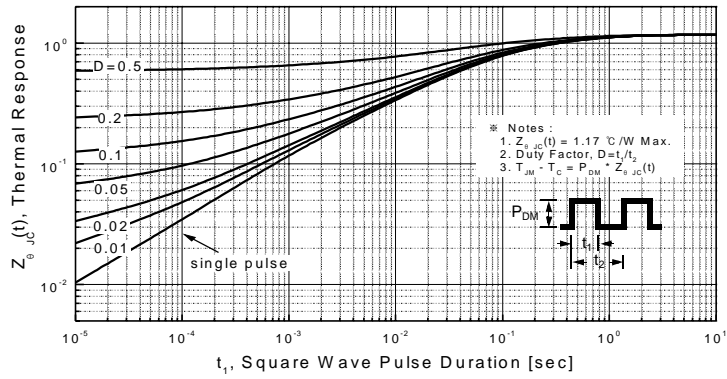


**Figure 9-2. Maximum Safe Operating Area for FQPF3N80C**

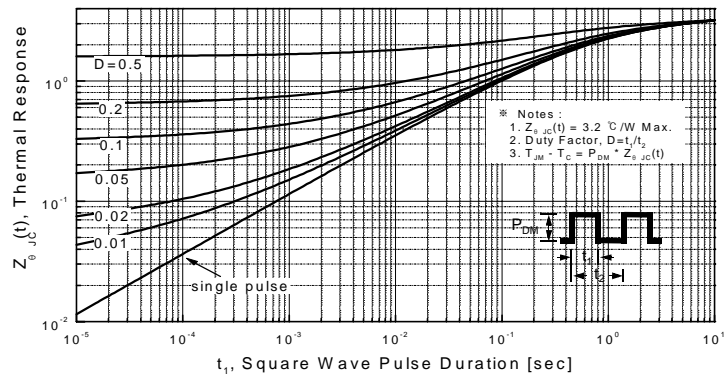


**Figure 10. Maximum Drain Current vs Case Temperature**

**Typical Characteristics** (Continued)

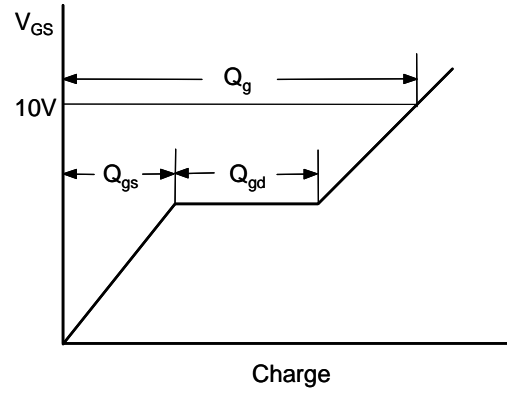
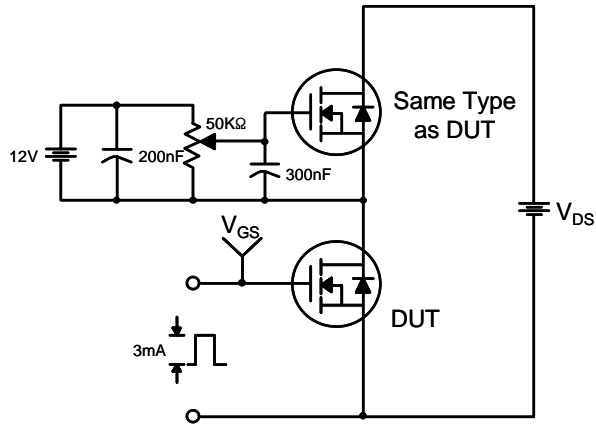


**Figure 11-1. Transient Thermal Response Curve for FQP3N80C**

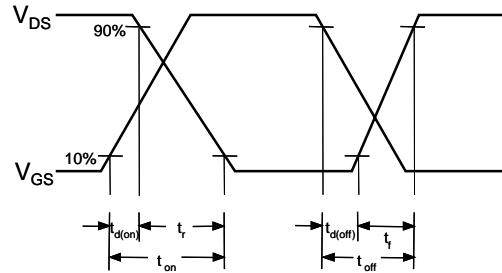
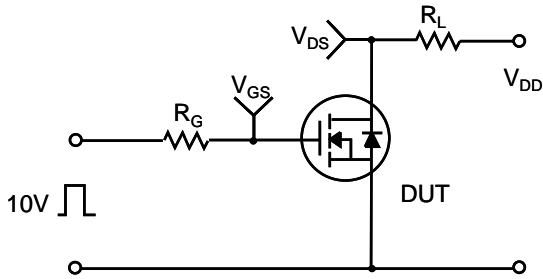


**Figure 11-2. Transient Thermal Response Curve for FQPF3N80C**

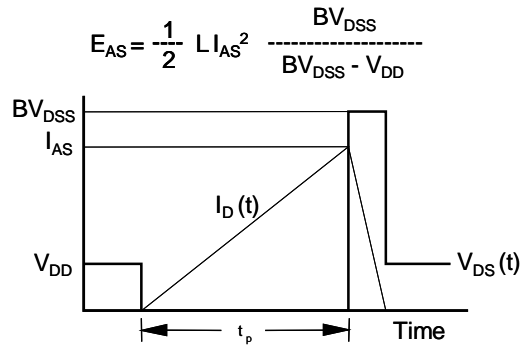
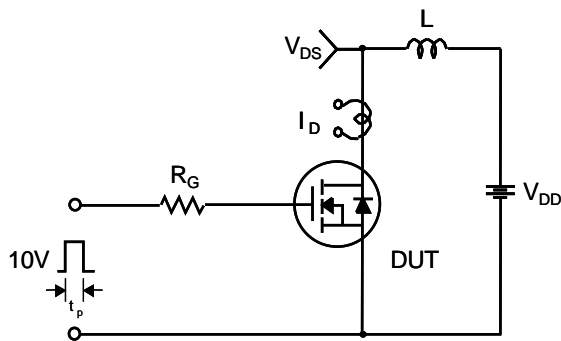
**Gate Charge Test Circuit & Waveform**



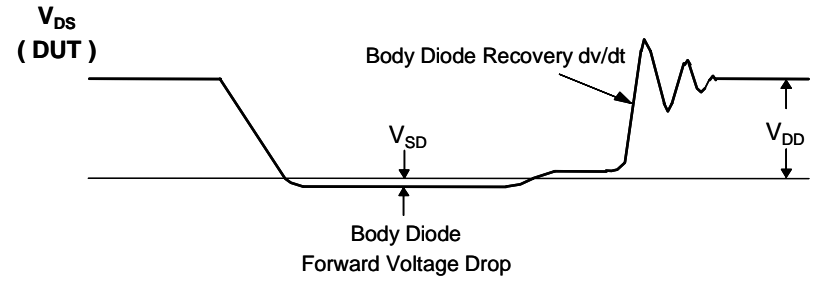
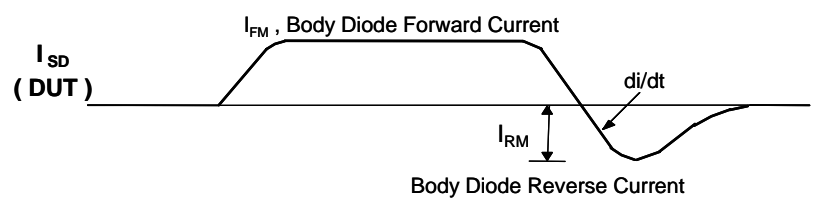
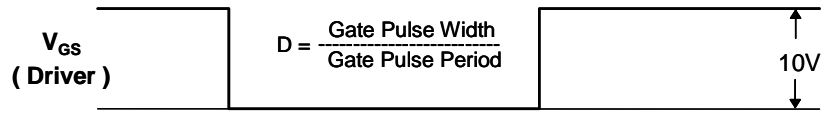
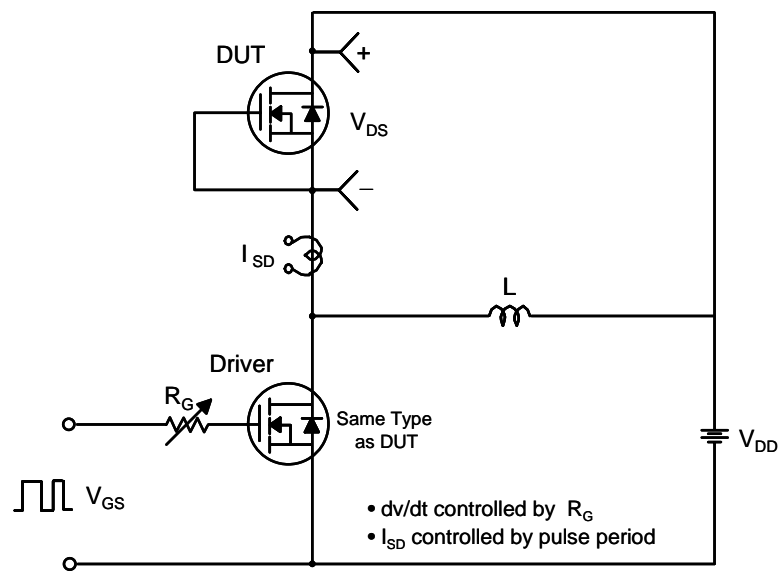
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveforms**

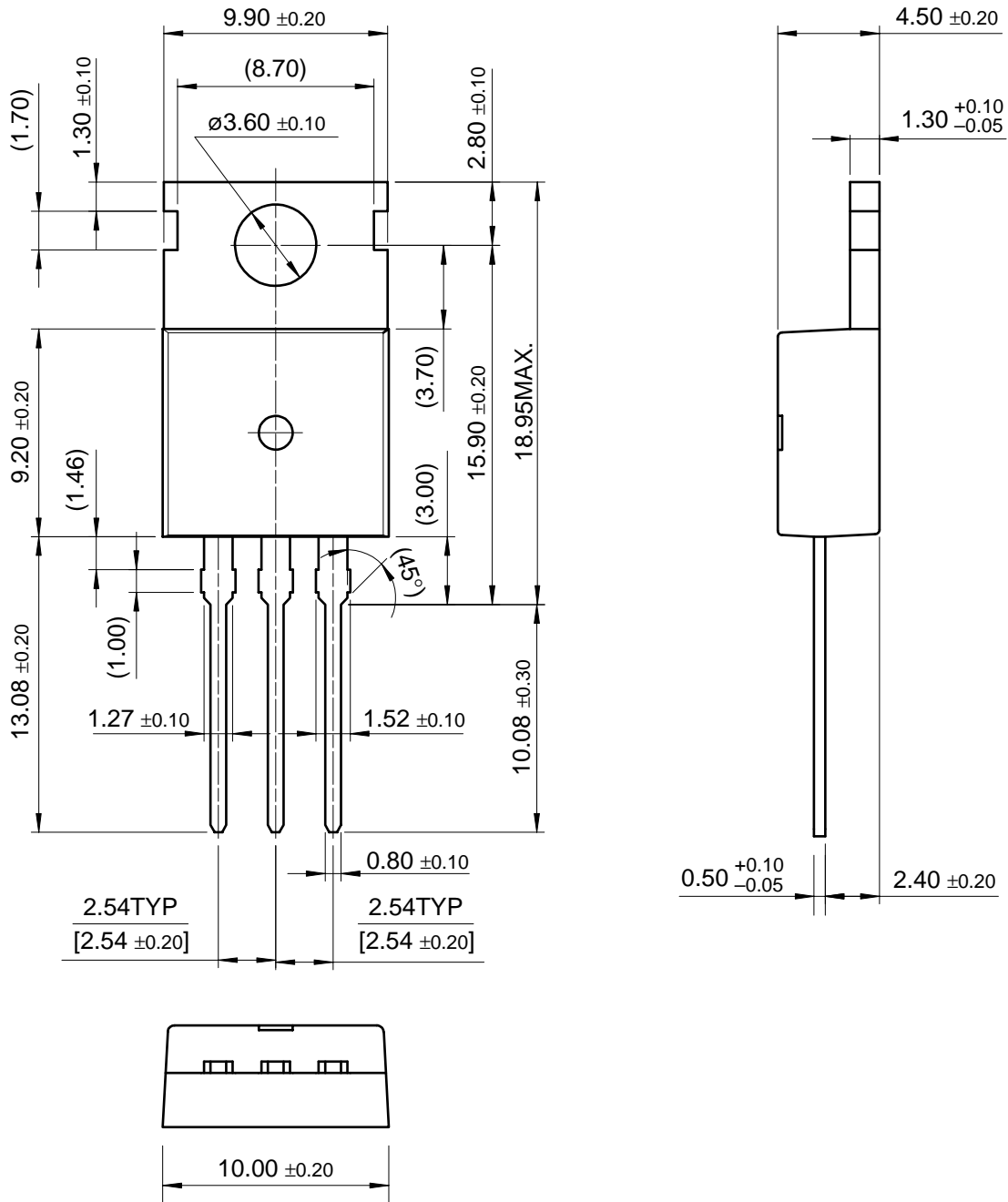


Peak Diode Recovery dv/dt Test Circuit & Waveforms



# Package Dimensions

## TO-220



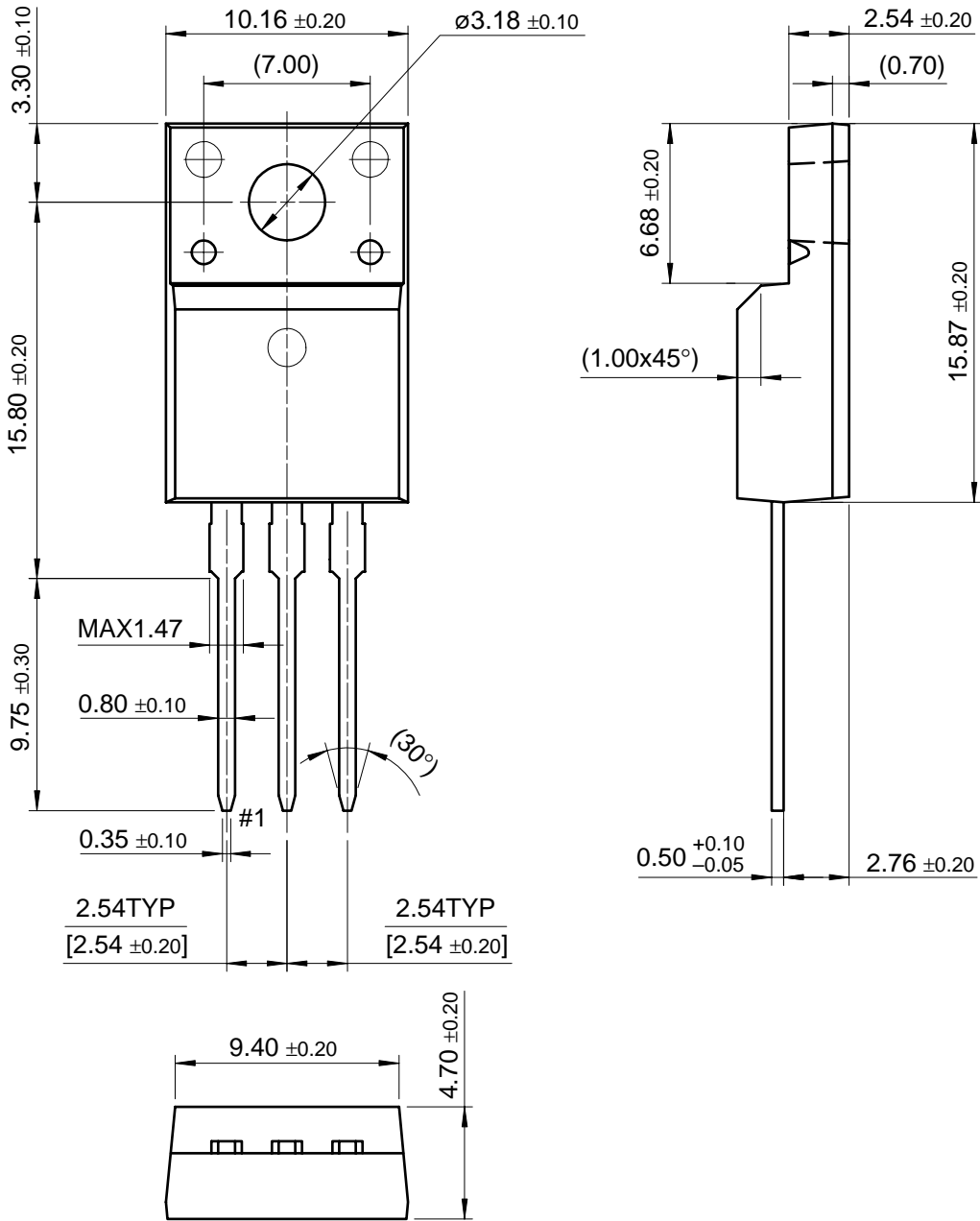
FQP3N80C/FQP3N80C

Dimensions in Millimeters



Package Dimensions (Continued)

TO-220F



FQP3N80C/FQP3N80C

Dimensions in Millimeters

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EcoSPARK™	GTO™	MSX™	QT Optoelectronics™	TinyLogic®
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